

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	700	V
Gate-Source Voltage	V_{GS}	± 30	V
Drain Current	$I_D(T_c=25^{\circ}\text{C})$	4.0	A
Drain Current	$I_D(T_c=100^{\circ}\text{C})$	2.5	A
Drain Current - Pulsed	$I_{DM}^{①}$	16	A
Single Pulsed Avalanche Energy	$E_{AS}^{②}$	260	mJ
Power Dissipation	P_{tot}	36	W
Junction Temperature Range	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^{\circ}\text{C}$
Junction-to-Case	$R_{\theta JC}$	3.47	$^{\circ}\text{C/W}$
Junction-to-Ambient	$R_{\theta JA}$	62.5	$^{\circ}\text{C/W}$

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	700			V
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS} / \Delta T_j$	$I_D=250\mu A$ Referenced to 25°C		0.65		$V/^{\circ}\text{C}$
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}$ $I_D=250\mu A$	2.0		4.0	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=700V$ $V_{GS}=0V$ $T_j=25^{\circ}\text{C}$			1	μA
		$V_{DS}=560V$ $V_{GS}=0V$ $T_j=125^{\circ}\text{C}$			10	μA
Forward Transconductance	g_{FS}	$V_{DS}=40V$ $I_D=2.0A^{③}$		4.0		S
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 30V$			± 100	nA
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=2.0A^{③}$		1.93	2.2	Ω
Input Capacitance	C_{iss}	$V_{GS}=0V$ $V_{DS}=25V$ $V_F=1.0MHz$		520		pF
Turn-Off Delay Time	$t_{d(off)}$	$V_{DD}=350V$ $I_D=4.0A$ $R_G=25\Omega^{③}$		25		ns

/ Electrical Characteristics(Ta=25)

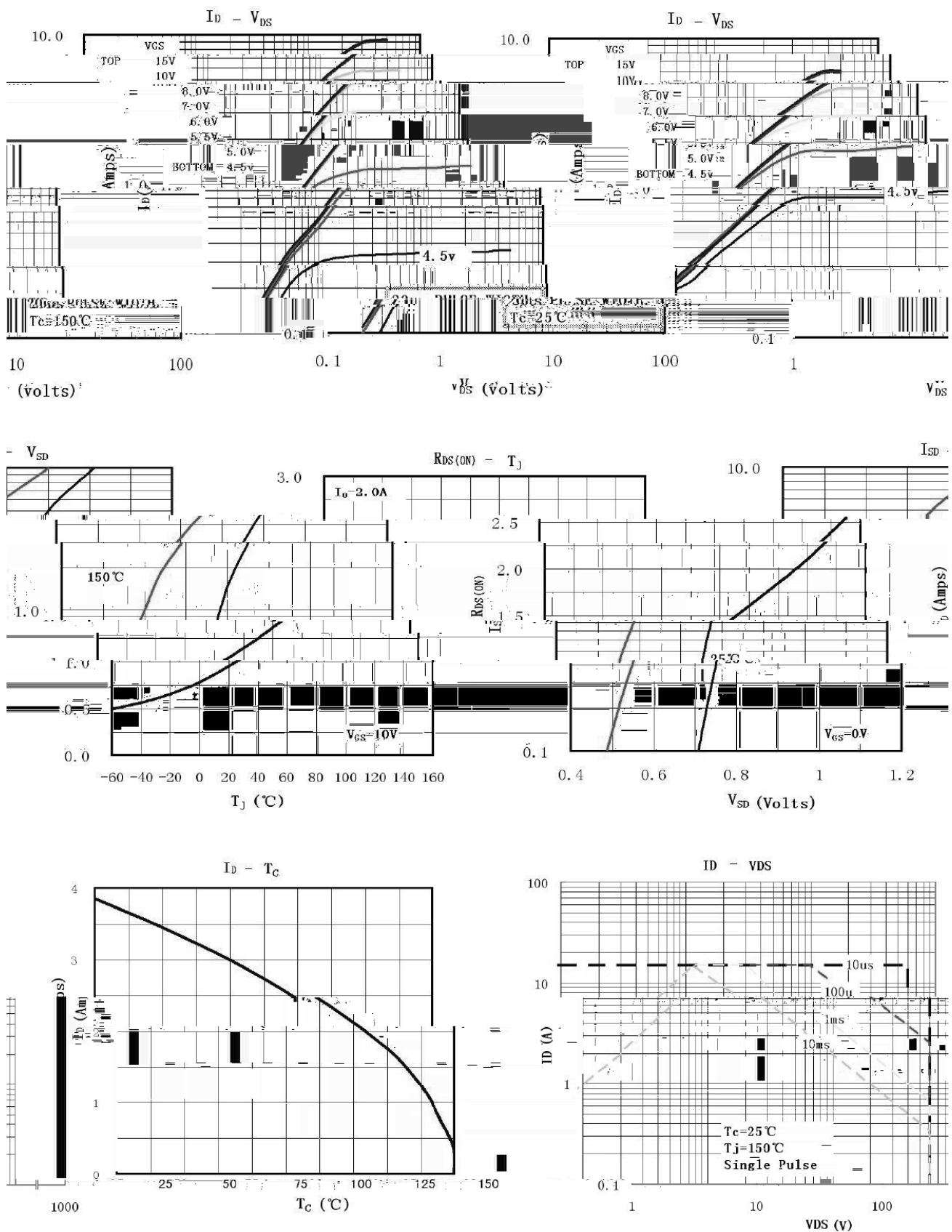
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	Q_g	$I_D=4.0A$ $V_{DS}=560V$ $V_{GS}=10V^{③}$		17.4		nC
Gate-to-Source Charge	Q_{gs}			4.8		nC
Gate-to-Drain Charge	Q_{gd}			5.4		nC
Continuous Diode Forward Current	I_S				4.0	A
Diode Forward Voltage	V_{SD}	$I_S=4.0A$ $V_{GS}=0V^{③}$ $T_J=25^{\circ}C$			1.4	V
Reverse Recovery Time	t_{rr}	$I_f=4.0A$ $T_J=25^{\circ}C$ $di/dt=100A/\mu s^{③}$		250		nS
Reverse Recovery Charge	Q_{rr}			1.5		uC

Repetitive rating: Pulse width limited by maximum junction temperature

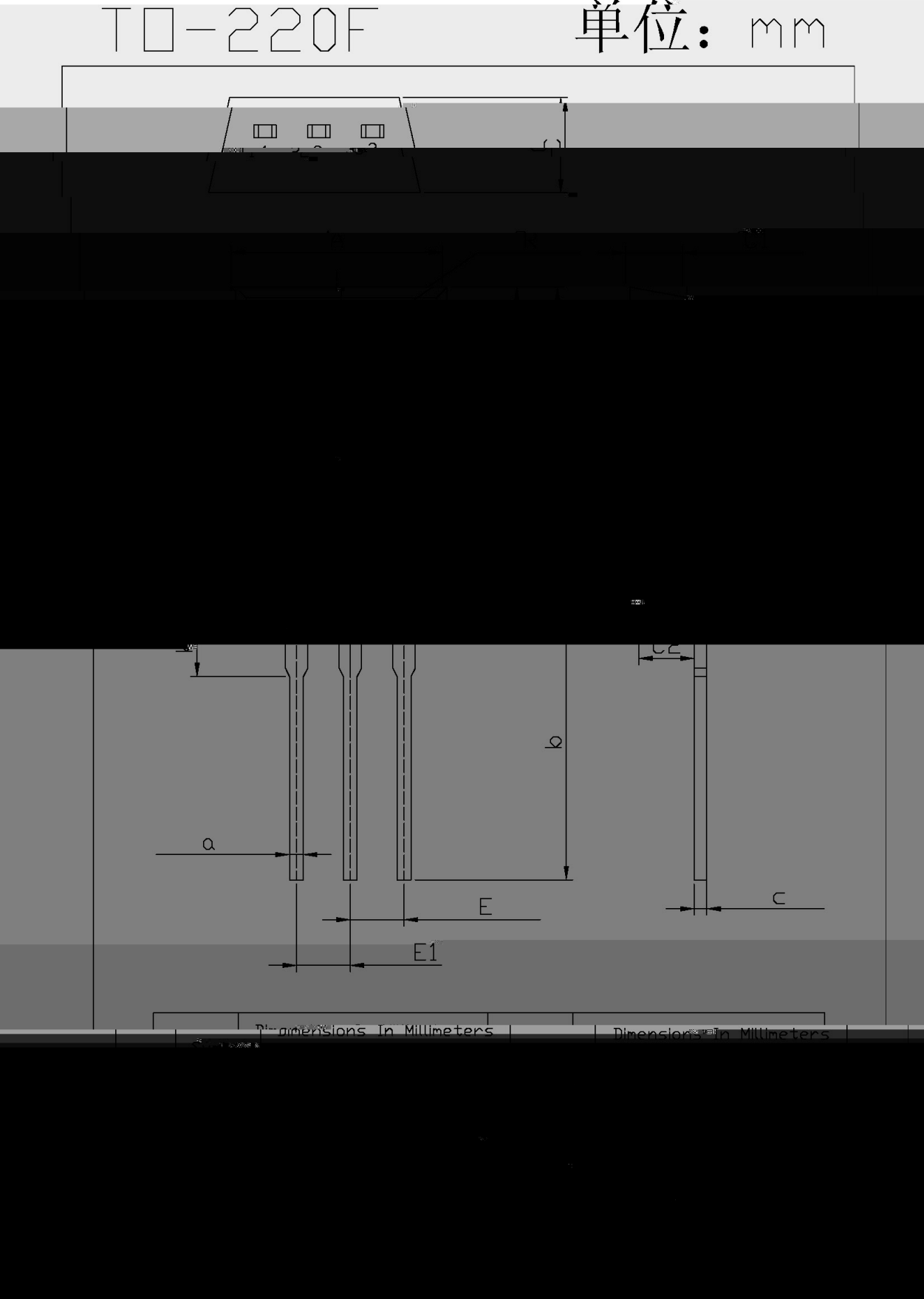
Starting $T_J=25$, $V_{DD}=50V$, $L=30mH$, $R_G=25\Omega$, $I_{AS}=4.0A$

Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$

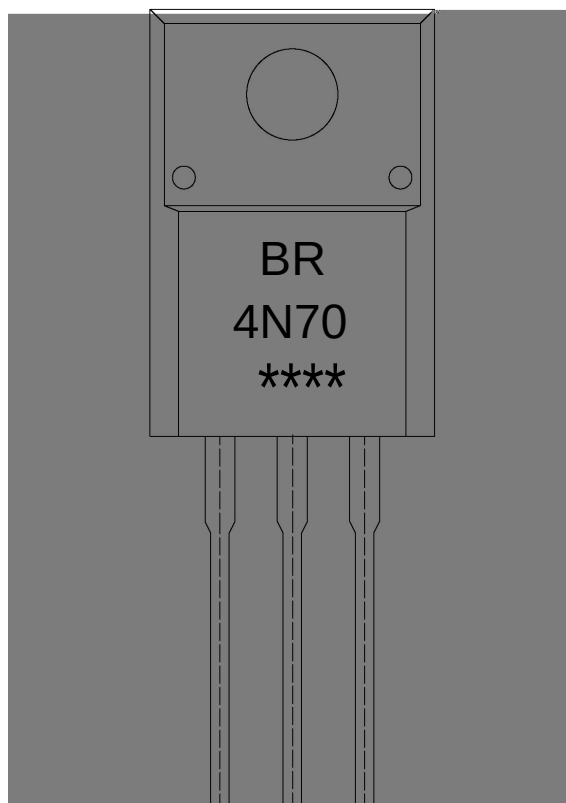
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR
4N70

Note:

BR: Company Code

4N70: Product Type.

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-----|-----|----|----------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255 | 5 | 5 | 0.5sec; | 2.Peak Temp.:255 5 , Duration:5 0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270 5 10 1 sec. Temp.:270±5℃ Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension (unit mm ³)		
	Units/Bag /	Bags/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Bag	Inner Box	Outer Box
TO-220/F	200	10	2,000	5	10,000	135×190	237×172×102	560×245×195

/ TUBE

Package Type	Units					Dimension (unit mm ³)		
	Units/Tube /	Tubes/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Tube	Inner Box	Outer Box
TO-220/F	50	20	1,000	5	5,000	532×31.4×5.5	555×164×50	575×290×180

/ Notices